these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please amend claims 4, 76, and 81 as follows:

4. (Thrice Amended) A method of passivating a conductive material, comprising:

providing said conductive material, wherein said conductive material has an ability to associate with oxygen; and

directly exposing said conductive material to a material selected from the group consisting of diborane, phosphine, methylsilane, hexamethyldisilane, and hexamethyldisilazane.

76. (Twice Amended) A method of passivating a conductive layer, comprising:

providing a tungsten nitride layer;

providing a polysilicon layer on the tungsten nitride layer; and

exposing the tungsten nitride layer to a material selected from the group consisting of diborane, phosphine, methylsilane, hexamethyldisilane, and hexamethyldisilazane.

81. (Twice Amended) A method of passivating a conductive layer, comprising:

providing a first conductive plug;

providing a first conductive layer on the plug;